**Editorial comments:**  
  
The manuscript has been modified and the updated manuscript, **58113\_R2.docx**, is attached and located in your Editorial Manager account. **Please use the updated version to make your revisions.**  
  
Unfortunately, there are a few sections of the manuscript that show significant overlap with previously published work. Though there may be a limited number of ways to describe a technique, please use original language throughout the manuscript. Please check the iThenticateReport attached to this email and revise the following lines: 50-63, 92-95, 384-396, 400-401, 445-447.

Answer: We noticed that there are some overlaps with our previously published paper; we have revised the mentioned lines according to the iThenticateReport. We have to point out that some expressions are standard terminology that universally used in the literature, for example heterostructure field effect transistors (HFETs), two-dimensional electron gas (2DEG), molecular beam epitaxy (MBE), MOCVD, SEM, TEM, and so on. These expressions can’t be deemed as overlap. The same applied to standard descriptions of various measurement procedures, as an example, “temperature dependent Hall effect measurements” or “Hall effect measurements in the van der Pauw configuration/geometry” etc. Therefore, during revision procedure, we made sure that there are no long phrases (more than 10 words in chain) overlapping with our previous articles.